

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>			Complete if Known	
	Application Number	10/581,950-Conf. #8737		
	Filing Date	August 18, 2008		
	First Named Inventor	Anderson		
	Art Unit	2822		
	Examiner Name	D. T. Nguyen		
	Attorney Docket Number	GWS-008		
Sheet	1	of	1	

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A12*	US-5,945,730	08-31-1999	Sicard et al.	
	A13*	US-6,261,944	07-17-2001	Mehta et al.	
	A14*	US-6,507,070	01-14-2003	Shen et al.	
	A15*	US-6,586,323	07-01-2003	Fan et al.	
	A16*	US-6,674,157	01-06-2004	Lang	
	A17*	US-6,861,702	03-01-2005	Kitamura et al.	
	A18*	US-6,936,923	08-30-2005	Lin et al.	
	A19*	US-7,432,595	10-07-2008	Okada	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ² -Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
	B1	WO-2005-057617 A3	06-23-2005	Great Wall Semiconductor	

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
	C4	Darwish et al., "Scaling Issues in Lateral Power MOSFETs," Proc. 1998 Intl. Symp. On Power Semiconductor Devices & Ics, pp. 329-332.		
	C5	International Search Report and Written Opinion for PCT/US2004/040698, dated August 8, 2005.		
	C6	International Search Report and Written Opinion for PCT/US2004/40197, mailed November 21, 2008.		
	C7	Pavler et al., "Bi-directional FlipFET™ MOSFETS for Cell Phone Battery Protection Circuits," PCIM 2001.		
	C8	Shen et al., "Lateral Discrete Power MOSFET: Enabling Technology for Next-Generation, MHz-Frequency, High-Density DC/DC Converters," APEC (2004).		
	C9	Sun et al., "0.35µm, 43 µA/cm ² 6mΩ Power MOSFET to Power Future Microprocessor," IEEE pp. 77-79 (1999).		
Examiner Signature			Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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